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The present invention relates to a method for processing a semiconductor substrate. More specifically, the invention relates to a method for etching a nitride film. Nitride semiconductor materials have good thermal conductivity, thermal stability, high electron saturation velocity, and other properties that are quite different from those of materials which are used in the current mainstream of semiconductor materials. Therefore, use of nitride semiconductors as materials for light-emitting devices is being investigated, and a nitride semiconductor layer is already actually used in light-emitting diodes (LEDs) and semiconductor lasers. Nitride semiconductors have a structure in which a nitride semiconductor layer is disposed on a substrate having an Al₂O₃ buffer layer thereon. At this time, a masking layer is formed on the nitride semiconductor layer and then a reaction gas is supplied onto the surface of the nitride semiconductor layer. According to the method, removal of the buffer layer, nitride semiconductor layer, and masking layer may be performed in one step. For this reason, an etching gas having a high etching rate for Al₂O₃ is generally selected and used. However, since Al₂O₃ has a high refractive index, the wavelength of light emitted from a light-emitting device based on nitride semiconductors may be decreased. As described above, as well, in a case where the substrate is composed of a single-crystalline nitride semiconductor layer, an etching damage tends to be easily caused in the substrate. Accordingly, in the method disclosed in Japanese Patent Application Publication No. 2008-217981, for example, instead of the single-crystalline nitride semiconductor layer, a single-crystalline silicon substrate on which a nitride semiconductor layer is formed is etched using the nitride semiconductor layer as a mask layer.
Q: Simple, complete and accurate □□□? My Japanese teacher wants me to use □□□ when teaching my class, when I find him to be better for discussion and asking questions, I am quite stuck on what to use. He won't tell me, so I have no basis to go on. c6a93da74d

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